

ZXMHC3A01T8

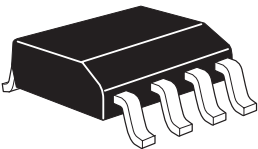
COMPLEMENTARY 30V ENHANCEMENT MODE MOSFET H-BRIDGE

SUMMARY

N-Channel = $V_{(BR)DSS} = 30V$: $R_{DS(on)} = 0.12\Omega$; $I_D = 3.1A$
P-Channel = $V_{(BR)DSS} = -30V$: $R_{DS(on)} = 0.21\Omega$; $I_D = -2.3A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



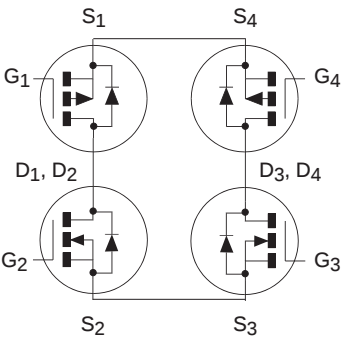
SM8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Single SM-8 surface mount package

APPLICATIONS

- Single phase DC fan motor drive



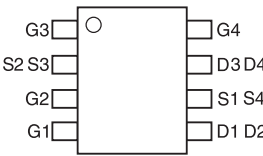
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMHC3A01T8TA	7"	12mm	1,000 units
ZXMHC3A01T8TC	13"	12mm	4,000 units

DEVICE MARKING

- ZXMH
C3A01

PINOUT



Top View

ZXMHC3A01T8

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	N-Channel	P-channel	UNIT
Drain-source voltage	V_{DSS}	30	-30	V
Gate-source voltage	V_{GS}	± 20	± 20	V
Continuous drain current ($V_{GS}=10V$; $T_A=25^\circ C$) ^{(b)(d)} ($V_{GS}=10V$; $T_A=70^\circ C$) ^{(b)(d)} ($V_{GS}=10V$; $T_A=25^\circ C$) ^{(a)(d)}	I_D	3.1	-2.3	A
		2.5	-1.8	A
		2.7	-2.0	A
Pulsed drain current ^(c)	I_{DM}	14.5	-10.8	A
Continuous source current (body diode) ^(b)	I_S	2.3	-2.2	A
Pulsed source current (body diode) ^(c)	I_{SM}	14.5	-10.8	A
Power dissipation at $T_A=25^\circ C$ ^{(a)(d)}	P_D	1.3		W
Linear derating factor		10.4		mW/ $^\circ C$
Power dissipation at $T_A=25^\circ C$ ^{(b)(d)}	P_D	1.7		W
Linear derating factor		13.6		mW/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		$^\circ C$

THERMAL RESISTANCE

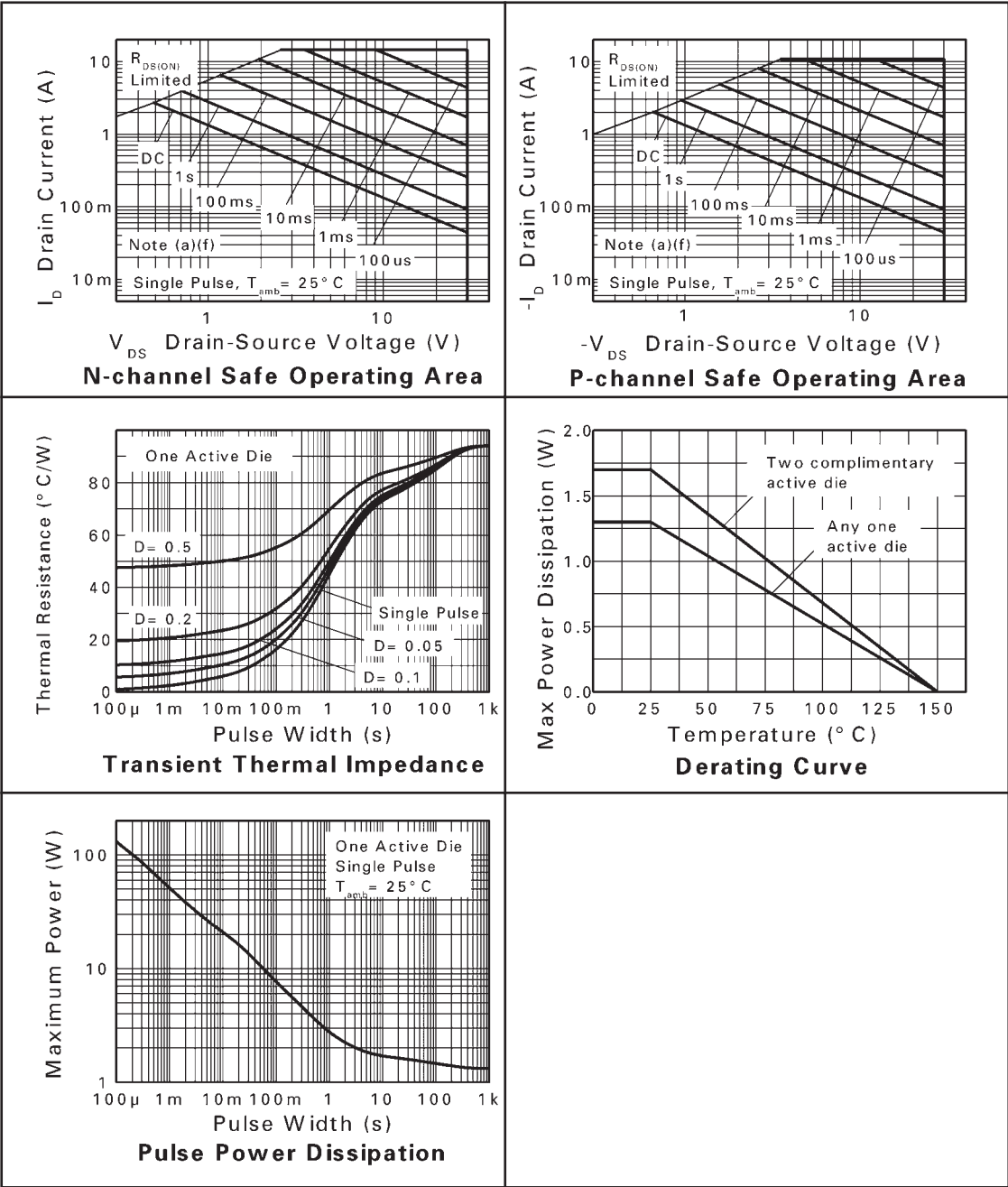
PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient ^{(a)(d)}	$R_{\theta JA}$	96	$^\circ C/W$
Junction to ambient ^{(b)(d)}	$R_{\theta JA}$	73	$^\circ C/W$

NOTES

- (a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
(c) Repetitive rating on 50mm x 50mm x 1.6mm FR4, $D=0.02$, pulse width 300 μ S - pulse width limited by maximum junction temperature. Refer to transient thermal impedance graph.
(d) For device with one active die.

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CHARACTERISTICS



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N-channel

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-source breakdown voltage	V _{(BR)DSS}	30			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			1.0	μA	V _{DS} =30V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	1.0		3.0	V	I _D = 250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ⁽¹⁾	R _{DS(on)}			0.12	Ω	V _{GS} = 10V, I _D = 2.5A
				0.18	Ω	V _{GS} = 4.5V, I _D = 2.0A
Forward transconductance ⁽¹⁾ ⁽³⁾	g _{fs}		3.5		S	V _{DS} =4.5V, I _D = 2.5A
DYNAMIC ⁽³⁾						
Input capacitance	C _{iss}		190		pF	V _{DS} = 25V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		38		pF	
Reverse transfer capacitance	C _{rss}		20		pF	
SWITCHING ⁽²⁾ ⁽³⁾						
Turn-on-delay time	t _{d(on)}		1.7		ns	V _{DD} = 15V, I _D = 2.5A R _G ≡ 6.0Ω, V _{GS} = 10V
Rise time	t _r		2.3		ns	
Turn-off delay time	t _{d(off)}		6.6		ns	
Fall time	t _f		2.9		ns	
Total gate charge	Q _g		3.9		nC	V _{DS} = 15V, V _{GS} = 10V I _D = 2.5A
Gate-source charge	Q _{gs}		0.6		nC	
Gate drain charge	Q _{gd}		0.9		nC	
SOURCE-DRAIN DIODE						
Diode forward voltage ⁽¹⁾	V _{SD}			0.95	V	T _j =25°C, I _S = 1.7A, V _{GS} =0V
Reverse recovery time ⁽³⁾	t _{rr}		17.7		ns	T _j =25°C, I _S = 2.5A,
Reverse recovery charge ⁽³⁾	Q _{rr}		13.0		nC	di/dt=100A/μs

NOTES

(1) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

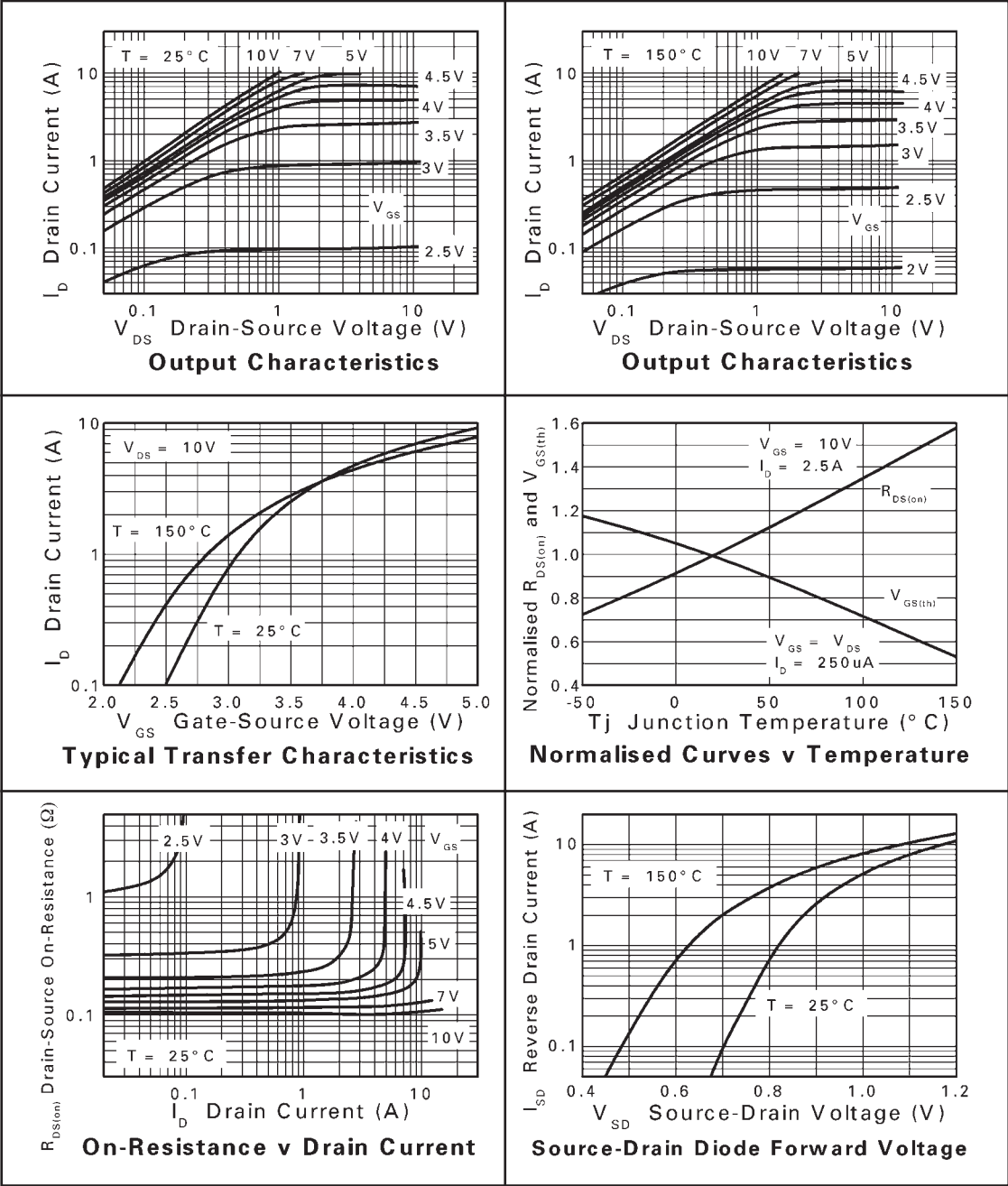
(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

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N-channel

TYPICAL CHARACTERISTICS



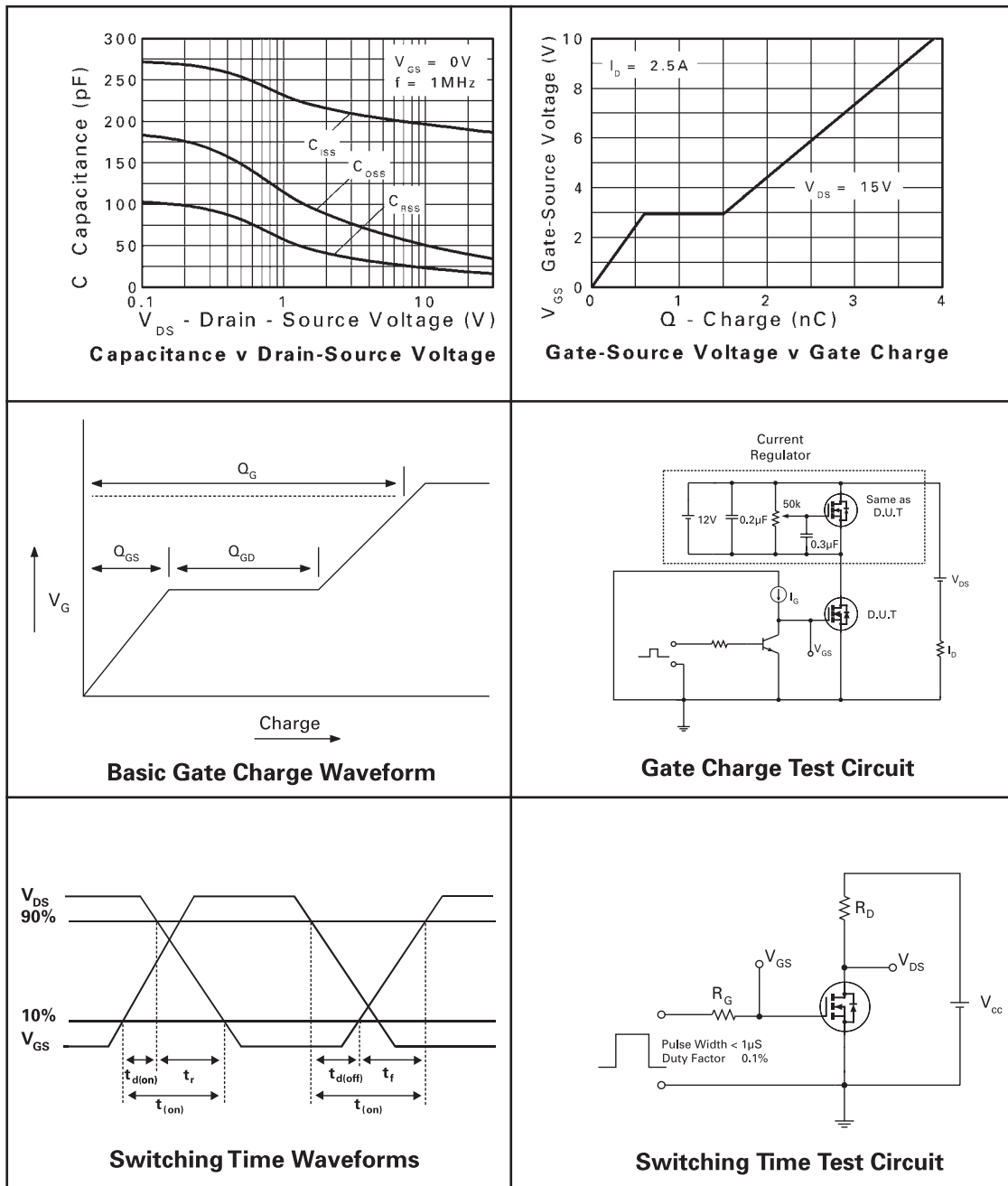
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N-channel

TYPICAL CHARACTERISTICS



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P-channel

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-source breakdown voltage	V _{(BR)DSS}	-30			V	I _D = -250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			-1.0	μA	V _{DS} = -30V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	-1.0		-3.0	V	I _D = -250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ⁽¹⁾	R _{DS(on)}			0.21	Ω	V _{GS} = -10V, I _D = -1.4A
				0.33	Ω	V _{GS} = -4.5V, I _D = -1.1A
Forward transconductance ⁽¹⁾ ⁽³⁾	g _{fs}		2.5		S	V _{DS} = -15V, I _D = -1.4A
DYNAMIC ⁽³⁾						
Input capacitance	C _{iss}		204		pF	V _{DS} = -15V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		39.8		pF	
Reverse transfer capacitance	C _{rss}		25.8		pF	
SWITCHING ⁽²⁾ ⁽³⁾						
Turn-on-delay time	t _{d(on)}		1.2		ns	V _{DD} = -15V, I _D = -1A R _G ≡ 6.0Ω, V _{GS} = -10V
Rise time	t _r		2.3		ns	
Turn-off delay time	t _{d(off)}		12.1		ns	
Fall time	t _f		7.5		ns	
Total gate charge			2.6		nC	V _{DS} = -15V, V _{GS} = -5V I _D = -1.4A V _{DS} = -15V, V _{GS} = -10V I _D = -1.4A
Total gate charge	Q _g		5.2		nC	
Gate-source charge	Q _{gs}		0.7		nC	
Gate drain charge	Q _{gd}		0.9		nC	
SOURCE-DRAIN DIODE						
Diode forward voltage ⁽¹⁾	V _{SD}		-0.85	-0.95	V	T _j =25°C, I _S = -1.1A, V _{GS} =0V
Reverse recovery time ⁽³⁾	t _{rr}		19		ns	T _j =25°C, I _S = -0.95A,
Reverse recovery charge ⁽³⁾	Q _{rr}		15		nC	di/dt=100A/μs

NOTES

(1) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

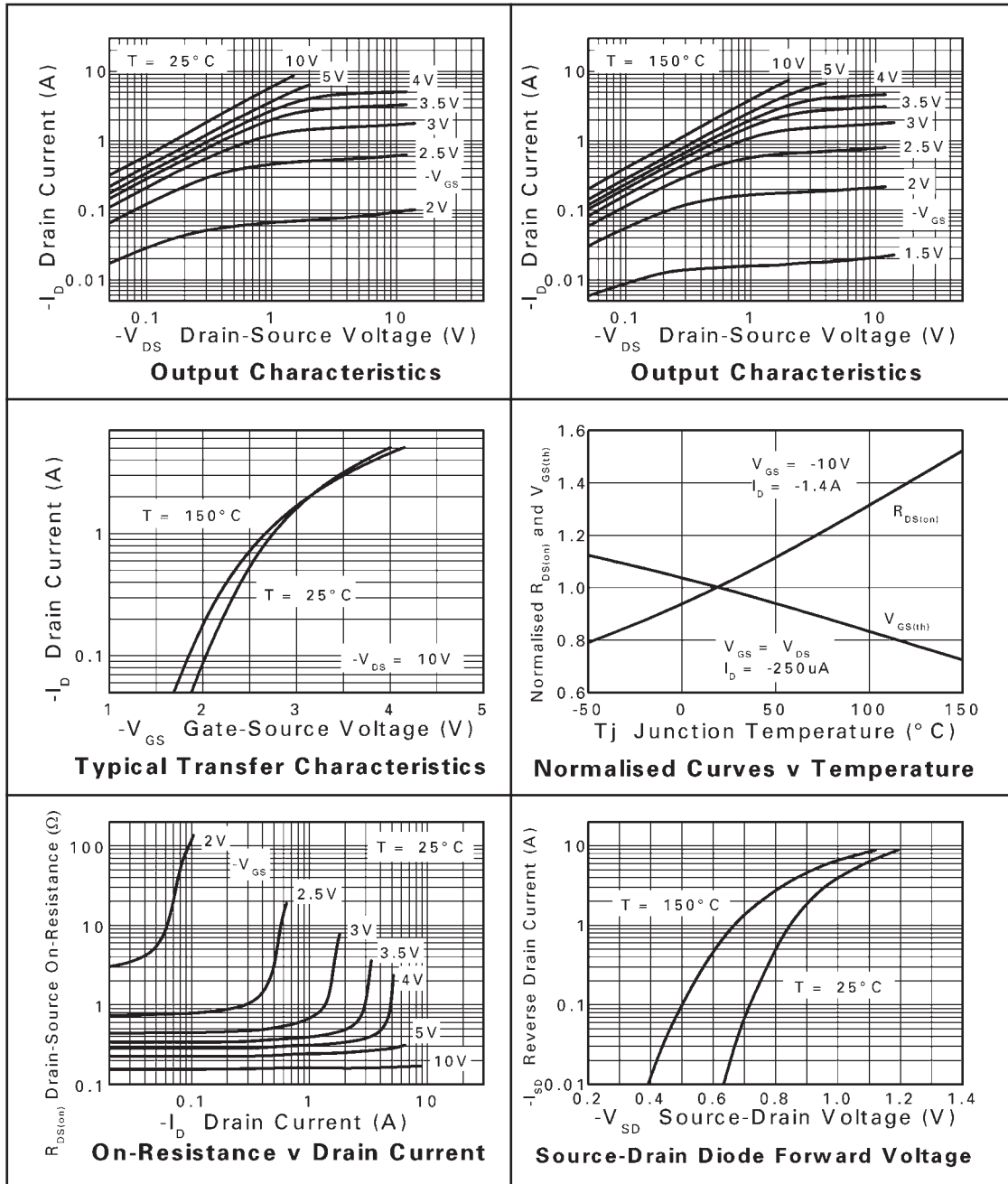
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P-channel

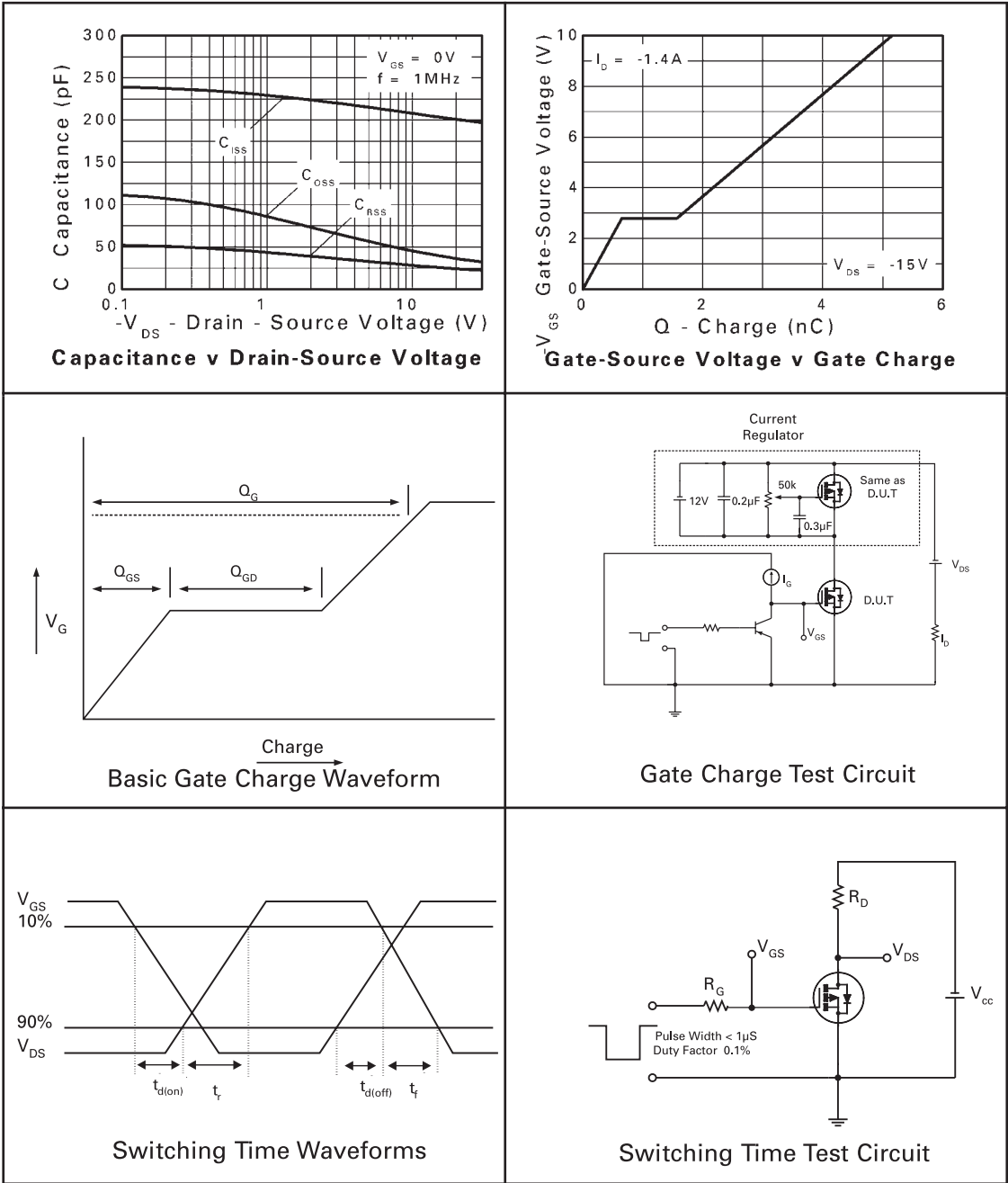
TYPICAL CHARACTERISTICS



ZXMHC3A01T8

P-channel

TYPICAL CHARACTERISTICS

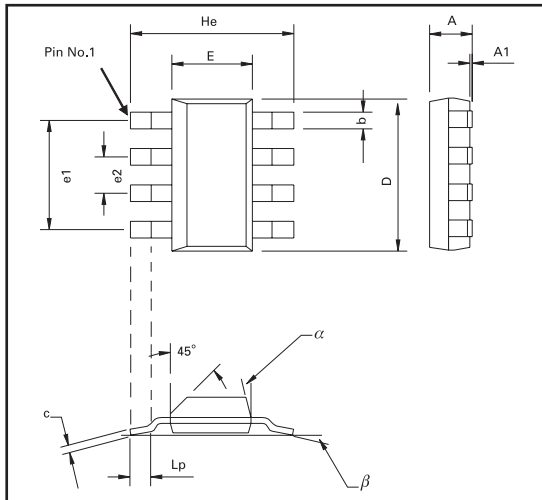


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PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimeters			Inches			DIM	Millimeters			Inches		
	Min	Max	Typ.	Min	Max	Typ.		Min	Max	Typ.	Min	Max	Typ.
A	-	1.7	-	-	0.067	-	e1	-	-	4.59	-	-	0.1807
A1	0.02	0.1	-	0.008	0.004	-	e2	-	-	1.53	-	-	0.0602
b	-	-	0.7	-	-	0.0275	He	6.7	7.3	-	0.264	0.287	-
c	0.24	0.32	-	0.009	0.013	-	Lp	0.9	-	-	0.035	-	-
D	6.3	6.7	-	0.248	0.264	-	alpha	-	15°	-	-	15°	-
E	3.3	3.7	-	0.130	0.145	-	beta	-	-	10°	-	-	10°

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